

# Peter J Wellmann

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

145  
papers

1,084  
citations

19  
h-index

26  
g-index

173  
ext. papers

1,274  
ext. citations

1.4  
avg, IF

4.65  
L-index

#	Paper	IF	Citations
145	Determination of site occupancy of boron in 6H-SiC by multiple-wavelength neutron holography. <i>Applied Physics Letters</i> , <b>2022</b> , 120, 132101	3.4	1
144	Influence of the growth conditions on the formation of macro-steps on the growth interface of SiC-Crystals. <i>Journal of Crystal Growth</i> , <b>2021</b> , 576, 126361	1.6	0
143	Status of 3 C - SiC Growth and Device Technology <b>2021</b> , 93-136		
142	Dislocation Formation During Physical Vapor Transport Growth of 4 H-SiC Crystals <b>2021</b> , 1-32		1
141	Novel Theoretical Approaches for Understanding and Predicting Dislocation Evolution and Propagation <b>2021</b> , 199-223		
140	Overgrowth of Protrusion Defects during Sublimation Growth of Cubic Silicon Carbide Using Free-Standing Cubic Silicon Carbide Substrates. <i>Crystal Growth and Design</i> , <b>2021</b> , 21, 4046-4054	3.5	3
139	The search for new materials and the role of novel processing routes. <i>Discover Materials</i> , <b>2021</b> , 1, 14		2
138	In Situ Visualization of the Ammonothermal Crystallization Process by X-ray Technology. <i>Springer Series in Materials Science</i> , <b>2021</b> , 171-190	0.9	
137	New Approaches and Understandings in the Growth of Cubic Silicon Carbide. <i>Materials</i> , <b>2021</b> , 14,	3.5	6
136	Special Equipment for Ammonothermal Processes. <i>Springer Series in Materials Science</i> , <b>2021</b> , 317-328	0.9	
135	Prospects of Bulk Growth of 3C-SiC Using Sublimation Growth. <i>Materials Science Forum</i> , <b>2020</b> , 1004, 113-119	1.9	4
134	Investigation of the Growth Kinetics of SiC Crystals during Physical Vapor Transport Growth by the Application of In Situ 3D Computed Tomography Visualization. <i>Advanced Engineering Materials</i> , <b>2020</b> , 22, 1900778	3.5	1
133	Intentional Incorporation and Tailoring of Point Defects during Sublimation Growth of Cubic Silicon Carbide by Variation of Process Parameters. <i>Physica Status Solidi (B): Basic Research</i> , <b>2020</b> , 257, 1900286	1.3	4
132	Influence of the growth interface shape on the defect characteristics in the facet region of 4H-SiC single crystals. <i>Journal of Crystal Growth</i> , <b>2020</b> , 532, 125436	1.6	7
131	On the importance of dislocation flow in continuum plasticity models for semiconductor materials. <i>Journal of Crystal Growth</i> , <b>2020</b> , 532, 125414	1.6	3
130	Epitaxial Metal Halide Perovskites by Inkjet-Printing on Various Substrates. <i>Advanced Functional Materials</i> , <b>2020</b> , 30, 2004612	15.6	10
129	Flow Stability, Convective Heat Transfer and Chemical Reactions in Ammonothermal Autoclaves Insights by In Situ Measurements of Fluid Temperatures. <i>Crystals</i> , <b>2020</b> , 10, 723	2.3	5

128	Impact of Varying Parameters on the Temperature Gradients in 100mm Silicon Carbide Bulk Growth in a Computer Simulation Validated by Experimental Results. <i>Crystal Research and Technology</i> , <b>2020</b> , 55, 1900121	1.3	3
127	Vacuum-Free and Highly Dense Nanoparticle Based Low-Band-Gap CuInSe <sub>2</sub> Thin-Films Manufactured by Face-to-Face Annealing with Application of Uniaxial Mechanical Pressure. <i>Coatings</i> , <b>2019</b> , 9, 484	2.9	1
126	Influence of Morphological Changes in a Source Material on the Growth Interface of 4h-SiC Single Crystals. <i>Materials</i> , <b>2019</b> , 12,	3.5	4
125	Modeling of the PVT Growth Process of Bulk 3C-SiC - Growth Process Development and Challenge of the Right Materials Data Base. <i>Materials Science Forum</i> , <b>2019</b> , 963, 157-160	0.4	3
124	Annealing-Induced Changes in the Nature of Point Defects in Sublimation-Grown Cubic Silicon Carbide. <i>Materials</i> , <b>2019</b> , 12,	3.5	2
123	Growth of Large-Area, Stress-Free, and Bulk-Like 3C-SiC (100) Using 3C-SiC-on-Si in Vapor Phase Growth. <i>Materials</i> , <b>2019</b> , 12,	3.5	7
122	Analysis of the Basal Plane Dislocation Density and Thermomechanical Stress during 100 mm PVT Growth of 4H-SiC. <i>Materials</i> , <b>2019</b> , 12,	3.5	7
121	Limitations during Vapor Phase Growth of Bulk (100) 3C-SiC Using 3C-SiC-on-SiC Seeding Stacks. <i>Materials</i> , <b>2019</b> , 12,	3.5	5
120	Optimization of the SiC Powder Source Size Distribution for the Sublimation Growth of Long Crystals Boules. <i>Materials Science Forum</i> , <b>2019</b> , 963, 42-45	0.4	1
119	Tracking of the Growth Interface during PVT-Growth of SiC Boules Using a X-Ray Computed Tomography Setup. <i>Materials Science Forum</i> , <b>2019</b> , 963, 14-17	0.4	1
118	Deep Electronic Levels in n-Type and p-Type 3C-SiC. <i>Materials Science Forum</i> , <b>2019</b> , 963, 297-300	0.4	2
117	Advances in In Situ SiC Growth Analysis Using Cone Beam Computed Tomography. <i>Materials Science Forum</i> , <b>2019</b> , 963, 5-9	0.4	1
116	Comparison of Achievable Contrast Features in Computed Tomography Observing the Growth of a 4H-SiC Bulk Crystal. <i>Materials</i> , <b>2019</b> , 12,	3.5	1
115	Vapor Growth of 3C-SiC Using the Transition Layer of 3C-SiC on Si CVD Templates. <i>Materials Science Forum</i> , <b>2019</b> , 963, 149-152	0.4	2
114	An adhesive bonding approach by hydrogen silsesquioxane for silicon carbide-based LED applications. <i>Materials Science in Semiconductor Processing</i> , <b>2019</b> , 91, 9-12	4.3	3
113	Solution Growth of Silicon Carbide Using the Vertical Bridgman Method. <i>Crystal Research and Technology</i> , <b>2018</b> , 53, 1800019	1.3	1
112	Growth Conditions and In Situ Computed Tomography Analysis of Facetted Bulk Growth of SiC Boules. <i>Materials Science Forum</i> , <b>2018</b> , 924, 245-248	0.4	
111	Review of SiC crystal growth technology. <i>Semiconductor Science and Technology</i> , <b>2018</b> , 33, 103001	1.8	36

110	Depth-resolved and temperature dependent analysis of phase formation processes in Cu <sub>2</sub> ZnSnSe films on ZnO substrates. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2017</b> , 28, 7730-7738	2.1	5
109	Ammonothermal Synthesis of Earth-Abundant Nitride Semiconductors ZnSiN and ZnGeN and Dissolution Monitoring by In Situ X-ray Imaging. <i>Chemistry - A European Journal</i> , <b>2017</b> , 23, 12275-12282	4.8	43
108	3C-SiC Bulk Sublimation Growth on CVD Hetero-Epitaxial Seeding Layers. <i>Materials Science Forum</i> , <b>2017</b> , 897, 15-18	0.4	1
107	Solubility and dissolution kinetics of GaN in supercritical ammonia in presence of ammonoacidic and ammonobasic mineralizers. <i>Journal of Crystal Growth</i> , <b>2017</b> , 479, 59-66	1.6	10
106	Growth, Defects and Doping of 3C-SiC on Hexagonal Polytypes. <i>ECS Journal of Solid State Science and Technology</i> , <b>2017</b> , 6, P741-P745	2	
105	Power Electronic Semiconductor Materials for Automotive and Energy Saving Applications - SiC, GaN, GaO, and Diamond. <i>Zeitschrift Fur Anorganische Und Allgemeine Chemie</i> , <b>2017</b> , 643, 1312-1322	1.3	36
104	(Invited) Growth, Defects and Doping of 3C-SiC on Hexagonal Polytypes. <i>ECS Transactions</i> , <b>2017</b> , 80, 107-115		1
103	Characterization of protrusions and stacking faults in 3C-SiC grown by sublimation epitaxy using 3C-SiC-on-Si seeding layers. <i>Advanced Materials Proceedings</i> , <b>2017</b> , 2, 774-778	1	2
102	Cubic silicon carbide as a potential photovoltaic material. <i>Solar Energy Materials and Solar Cells</i> , <b>2016</b> , 145, 104-108	6.4	32
101	Chemical stability of carbon-based inorganic materials for in situ x-ray investigations of ammonothermal crystal growth of nitrides. <i>Journal of Crystal Growth</i> , <b>2016</b> , 456, 33-42	1.6	8
100	Single Domain 3C-SiC Growth on Off-Oriented 4H-SiC Substrates. <i>Crystal Growth and Design</i> , <b>2015</b> , 15, 2940-2947	3.5	31
99	Low temperature formation of CuIn <sub>1-x</sub> Ga <sub>x</sub> Se <sub>2</sub> solar cell absorbers by all printed multiple species nanoparticulate Se + CuIn + CuGa precursors. <i>Thin Solid Films</i> , <b>2015</b> , 582, 60-68	2.2	1
98	Numerical reactive diffusion modeling of stacked elemental layer rapid thermal annealed chalcopyrite absorber layer formation. <i>Thin Solid Films</i> , <b>2015</b> , 582, 397-400	2.2	3
97	Quantitative Study of the Role of Supersaturation during Sublimation Growth on the Yield of 50 mm 3C-SiC. <i>Materials Science Forum</i> , <b>2015</b> , 821-823, 77-80	0.4	12
96	Characterization of kesterite thin films fabricated by rapid thermal processing of stacked elemental layers using spatially resolved cathodoluminescence. <i>Thin Solid Films</i> , <b>2015</b> , 582, 387-391	2.2	1
95	Synthesis of In <sub>2</sub> Se <sub>3</sub> and Cu <sub>2-x</sub> Se Micro- and Nanoparticles with Microwave-Assisted Solvothermal and Aqueous Redox Reactions for the Preparation and Stabilization of Printable Precursors for a CuInSe <sub>2</sub> Solar Cell Absorber Layer. <i>Energy Procedia</i> , <b>2015</b> , 84, 62-70	2.3	5
94	Towards the Growth of SiGeC Epitaxial Layers for the Application in Si Solar Cells. <i>Energy Procedia</i> , <b>2015</b> , 84, 236-241	2.3	3
93	Progress on Numerical Reactive Diffusion Modeling of CuInSe <sub>2</sub> Phase Formation for Solar Cell Applications. <i>Energy Procedia</i> , <b>2015</b> , 84, 86-92	2.3	

92	Determination of GaN solubility in supercritical ammonia with NH <sub>4</sub> F and NH <sub>4</sub> Cl mineralizer by in situ x-ray imaging of crystal dissolution. <i>Journal of Crystal Growth</i> , <b>2015</b> , 418, 64-69	1.6	19
91	Optimization of growth parameters for growth of high quality heteroepitaxial 3C-SiC films at 1200°C. <i>Thin Solid Films</i> , <b>2015</b> , 577, 88-93	2.2	10
90	Ceramic liner technology for ammonoacidic synthesis. <i>Journal of Supercritical Fluids</i> , <b>2015</b> , 99, 76-87	4.2	12
89	Growth of SiC bulk crystals for application in power electronic devices [process design, 2D and 3D X-ray in situ visualization and advanced doping. <i>Crystal Research and Technology</i> , <b>2015</b> , 50, 2-9	1.3	24
88	Formation of Cu <sub>2</sub> SnSe <sub>3</sub> from stacked elemental layers investigated by combined in situ X-ray diffraction and differential scanning calorimetry techniques. <i>Journal of Alloys and Compounds</i> , <b>2014</b> , 588, 254-258	5.7	12
87	Advances in wide bandgap SiC for optoelectronics. <i>European Physical Journal B</i> , <b>2014</b> , 87, 1	1.2	46
86	Real-Time Measurement of the Evolution of Growth Facets during SiC PVT Bulk Growth Using 3-D X-Ray Computed Tomography. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 9-12	0.4	1
85	Towards X-ray in-situ visualization of ammonothermal crystal growth of nitrides. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2014</b> , 11, 1439-1442		4
84	Morphological and Optical Stability in Growth of Fluorescent SiC on Low Off-Axis Substrates. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 19-22	0.4	1
83	Application of 3-D X-Ray Computed Tomography for the In Situ Visualization of the SiC Crystal Growth Interface during PVT Bulk Growth. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 27-30	0.4	1
82	Step-Flow Growth of Fluorescent 4H-SiC Layers on 4 Degree Off-Axis Substrates. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 185-188	0.4	3
81	Polycrystalline SiC as Source Material for the Growth of Fluorescent SiC Layers. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 39-42	0.4	8
80	Intermetallic compounds dynamic formation during annealing of stacked elemental layers and its influences on the crystallization of Cu <sub>2</sub> ZnSnSe <sub>4</sub> films. <i>Materials Chemistry and Physics</i> , <b>2013</b> , 142, 311-317	4.4	26
79	Photoluminescence Topography of Fluorescent SiC and its Corresponding Source Crystals. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 421-424	0.4	
78	In-situ phase formation study of copper indium diselenide absorber layers from CuIn nanoparticles and evaporated selenium. <i>Thin Solid Films</i> , <b>2013</b> , 535, 133-137	2.2	6
77	Microsecond Carrier Lifetimes in Bulk-Like 3C-SiC Grown by Sublimation Epitaxy. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 315-318	0.4	
76	Lateral Boron Distribution in Polycrystalline SiC Source Materials. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 397-400	0.4	1
75	Modeling of the Mass Transport during Homo-Epitaxial Growth of Silicon Carbide by Fast Sublimation Epitaxy. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 52-55	0.4	4

74	Fabrication of Broadband Antireflective Sub-Wavelength Structures on Fluorescent SiC. <i>Materials Science Forum</i> , <b>2013</b> , 740-742, 1024-1027	0.4	
73	Tuning the emission colour by manipulating terbium-terbium interactions: Terbium doped aluminum nitride as an example system. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 073518	2.5	19
72	Optimising The Parameters For The Synthesis Of CuIn-Nanoparticles By Chemical Reduction Method For Chalcopyrite Thin Film Precursors. <i>Materials Research Society Symposia Proceedings</i> , <b>2013</b> , 1538, 203-208		2
71	Nucleation Control of Cubic Silicon Carbide on 6H- Substrates. <i>Crystal Growth and Design</i> , <b>2012</b> , 12, 197-204	3.4	22
70	Freestanding 3C-SiC Grown by Sublimation Epitaxy Using 3C-SiC Templates on Silicon. <i>Materials Science Forum</i> , <b>2012</b> , 717-720, 177-180	0.4	1
69	Defect Structures at the Silicon/3C-SiC Interface. <i>Materials Science Forum</i> , <b>2012</b> , 717-720, 423-426	0.4	
68	Broadband and omnidirectional light harvesting enhancement of fluorescent SiC. <i>Optics Express</i> , <b>2012</b> , 20, 7575-9	3.3	13
67	Low-temperature processing of transparent conductive indium tin oxide nanocomposites using polyvinyl derivatives. <i>Thin Solid Films</i> , <b>2011</b> , 520, 1341-1347	2.2	13
66	Low temperature processing of hybrid nanoparticulate Indium Tin Oxide (ITO) polymer layers and application in large scale lighting devices. <i>Thin Solid Films</i> , <b>2011</b> , 519, 5744-5747	2.2	5
65	Fabrication, charge carrier transport, and application of printable nanocomposites based on indium tin oxide nanoparticles and conducting polymer 3,4-ethylenedioxythiophene/polystyrene sulfonic acid. <i>Journal of Applied Physics</i> , <b>2011</b> , 110, 104301	2.5	9
64	Efficient Image Segmentation for Detection of Dislocations in High Resolution Light Microscope Images of SiC Wafers. <i>Materials Science Forum</i> , <b>2011</b> , 679-680, 277-281	0.4	1
63	Generation of Void-Like Structures during Hot-Hydrogen Etching of Si Substrates for 3C-SiC Epitaxy. <i>Materials Science Forum</i> , <b>2011</b> , 679-680, 127-130	0.4	2
62	Fundamental Study of the Temperature Ramp-Up Influence for 3C-SiC Hetero-Epitaxy on Silicon (100). <i>Materials Science Forum</i> , <b>2010</b> , 645-648, 151-154	0.4	1
61	Observation of Lattice Plane Bending during SiC PVT Bulk Growth Using In Situ High Energy X-Ray Diffraction. <i>Materials Science Forum</i> , <b>2010</b> , 645-648, 29-32	0.4	9
60	Conductivity and adhesion enhancement in low-temperature processed indium tin oxide/polymer nanocomposites. <i>Thin Solid Films</i> , <b>2010</b> , 518, 2910-2915	2.2	21
59	Determination of material inhomogeneities in . <i>Energy Procedia</i> , <b>2010</b> , 2, 183-188	2.3	3
58	Germanium Incorporation during PVT Bulk Growth of Silicon Carbide. <i>Materials Science Forum</i> , <b>2009</b> , 615-617, 11-14	0.4	2
57	Real-time Investigations on the Formation of CuIn(S,Se) <sub>2</sub> while annealing precursors with varying sulfur content. <i>Materials Research Society Symposia Proceedings</i> , <b>2009</b> , 1165, 1		3

56	Photoluminescence-Topography of the p-Type Doped SiC Wafers for Determination of Doping Inhomogeneity. <i>Materials Science Forum</i> , <b>2009</b> , 615-617, 259-262	0.4	0
55	P- and n-Type Doping in SiC Sublimation Epitaxy Using Highly Doped Substrates. <i>Materials Science Forum</i> , <b>2009</b> , 615-617, 85-88	0.4	1
54	Conductance Enhancement Mechanisms of Printable Nanoparticulate Indium Tin Oxide (ITO) Layers for Application in Organic Electronic Devices. <i>Advanced Engineering Materials</i> , <b>2009</b> , 11, 295-301	3.5	27
53	In Situ Observation of Polytype Switches during SiC PVT Bulk Growth by High Energy X-Ray Diffraction. <i>Materials Science Forum</i> , <b>2009</b> , 615-617, 23-26	0.4	6
52	Bulk Growth of SiC. <i>Materials Research Society Symposia Proceedings</i> , <b>2008</b> , 1069, 1		0
51	Bulk growth of SiC [Review on advances of SiC vapor growth for improved doping and systematic study on dislocation evolution. <i>Physica Status Solidi (B): Basic Research</i> , <b>2008</b> , 245, 1239-1256	1.3	21
50	Determination of dislocation density in MOVPE grown GaN layers using KOH defect etching. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 955-958	1.6	11
49	Application of optical absorbance for the investigation of electronic and structural properties of sol-gel processed TiO <sub>2</sub> films. <i>Thin Solid Films</i> , <b>2008</b> , 516, 7256-7259	2.2	86
48	Cathodoluminescence characterization of organic semiconductor materials for light emitting device applications. <i>Journal of Applied Physics</i> , <b>2007</b> , 101, 113704	2.5	7
47	Electrical, optical and morphological properties of nanoparticle indium tin oxide layers. <i>Thin Solid Films</i> , <b>2007</b> , 515, 8567-8572	2.2	52
46	In Situ X-Ray Measurements of Defect Generation during PVT Growth of SiC. <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 267-270	0.4	6
45	Contactless Electrical Defect Characterization and Topography of a-Plane Grown Epitaxial Layers. <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 327-330	0.4	2
44	Impact of n-Type versus p-Type Doping on Mechanical Properties and Dislocation Evolution during SiC Crystal Growth. <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 259-262	0.4	2
43	Defect Etching of Non-Polar and Semi-Polar Faces in SiC. <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 243-246.	0.4	1
42	Influence of Growth Temperature on the Evolution of Dislocations during PVT Growth of Bulk SiC Single Crystals. <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 263-266	0.4	0
41	Growth and Characterization of <sup>13</sup> C Enriched 4H-SiC for Fundamental Materials Studies. <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 13-16	0.4	4
40	Silicon Carbide Growth: C/Si Ratio Evaluation and Modeling. <i>Materials Research Society Symposia Proceedings</i> , <b>2006</b> , 911, 2		
39	Basal Plane Dislocation Dynamics in Highly p-Type Doped versus Highly n-Type Doped SiC. <i>Materials Science Forum</i> , <b>2006</b> , 527-529, 79-82	0.4	4

38	Results of SIMS, LTPL and Temperature-Dependent Hall Effect Measurements Performed on Al-Doped SiC Substrates Grown by the M-PVT Method. <i>Materials Science Forum</i> , <b>2006</b> , 527-529, 633-636 <sup>0.4</sup>	0.4	6
37	Modeling and Experimental Verification of SiC M-PVT Bulk Crystal Growth. <i>Materials Science Forum</i> , <b>2006</b> , 527-529, 75-78	0.4	2
36	Electronic Raman Studies of Shallow Donors in Silicon Carbide. <i>Materials Science Forum</i> , <b>2006</b> , 527-529, 579-584	0.4	3
35	Progress and Limits of the Numerical Simulation of SiC Bulk and Epitaxy Growth Processes. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 3-8	0.4	3
34	SiC single crystal growth by a modified physical vapor transport technique. <i>Journal of Crystal Growth</i> , <b>2005</b> , 275, e555-e560	1.6	34
33	In situ visualization of SiC physical vapor transport crystal growth. <i>Journal of Crystal Growth</i> , <b>2005</b> , 275, e1807-e1812	1.6	20
32	Photoluminescence Study of In-Situ Rare Earth Doped PVT-Grown SiC Single Crystals. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 445-448	0.4	4
31	High Al-Doping of SiC Using a Modified PVT (M-PVT) Growth Set-Up. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 31-34	0.4	10
30	Development of a KOH Defect Etching Furnace with Absolute In-Situ Temperature Measurement Capability. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 283-286	0.4	5
29	Micro-Optical Characterization Study of Highly p-Type Doped SiC:Al Wafers. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 393-396	0.4	3
28	Modified Physical Vapor Transport Growth of SiC - Control of Gas Phase Composition for Improved Process Conditions. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 25-30	0.4	8
27	Structural Defects in SiC Crystals Investigated by High Energy X-Ray Diffraction. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 339-342	0.4	
26	In-Situ Er-Doping of SiC Bulk Single Crystals. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 723-726	0.4	1
25	On the Origin of the Below Band-Gap Absorption Bands in n-Type (N) 4H- and 6H-SiC. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 645-648	0.4	2
24	Growth of Phosphorous-Doped n-Type 6H-SiC Crystals using a Modified PVT Technique and Phosphine as Source. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 727-730	0.4	4
23	Analysis of Graphitization during Physical Vapor Transport Growth of Silicon Carbide. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 55-58	0.4	8
22	Investigation of Mass Transport during SiC PVT Growth Using Digital X-Ray Imaging, <sup>13</sup> C Labeling of Source Material and Numerical Modeling. <i>Materials Science Forum</i> , <b>2003</b> , 433-436, 9-12	0.4	6
21	Determination of Exciton Capture Cross-Sections of Neutral Nitrogen Donor on Cubic and Hexagonal Sites in n-Type (N) 6H-SiC. <i>Materials Science Forum</i> , <b>2003</b> , 433-436, 341-344	0.4	5



20	Electrical and Optical Characterization of p-Type Boron-Doped 6H-SiC Bulk Crystals. <i>Materials Science Forum</i> , <b>2003</b> , 433-436, 337-340	0.4	2
19	Impact of Compensation on Optical Absorption Bands in the Below-Bandgap Region in n-Type (N) 6H-SiC. <i>Materials Science Forum</i> , <b>2003</b> , 433-436, 333-336	0.4	5
18	Aluminum Doping of 6H- and 4H-SiC with a Modified PVT Growth Method. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 131-134	0.4	3
17	In Situ Synthesis of Source Material from Elemental Si and C during SiC PVT Growth Process and Characterization Using Digital X-Ray Imaging. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 91-94	0.4	2
16	Study of Boron Incorporation During PVT Growth of p-type SiC Crystals. <i>Materials Science Forum</i> , <b>2001</b> , 353-356, 49-52	0.4	9
15	Stability Criteria for 4H-SiC Bulk Growth. <i>Materials Science Forum</i> , <b>2001</b> , 353-356, 25-28	0.4	19
14	Numerical Simulation of Thermal Stress Formation During PVT-Growth of SiC Bulk Crystals. <i>Materials Science Forum</i> , <b>2001</b> , 353-356, 65-68	0.4	17
13	Investigation of a PVT SiC-Growth Set-up Modified by an Additional Gas Flow. <i>Materials Science Forum</i> , <b>2001</b> , 353-356, 33-36	0.4	13
12	Impact of SiC Source Material on Temperature Field and Vapor Transport During SiC PVT Crystal Growth Process. <i>Materials Science Forum</i> , <b>2001</b> , 353-356, 11-14	0.4	3
11	Absorption Measurements and Doping Level Evaluation in n-Type and p-Type 4H-SiC and 6H-SiC. <i>Materials Science Forum</i> , <b>2001</b> , 353-356, 397-400	0.4	5
10	SiC Crystal Growth from the Vapor and Liquid Phase. <i>Materials Research Society Symposia Proceedings</i> , <b>2000</b> , 640, 1		4
9	Digital X-Ray Imaging of SiC PVT Process: Analysis of Crystal Growth and Powder Source Degradation. <i>Materials Science Forum</i> , <b>2000</b> , 338-342, 71-74	0.4	4
8	Growth Rate Control in SiC-Physical Vapor Transport Method Through Heat Transfer Modeling and Non-Stationary Process Conditions. <i>Materials Science Forum</i> , <b>2000</b> , 338-342, 39-42	0.4	6
7	On the Excitation Mechanism of Erbium and Ytterbium in the Quaternary Compounds InGaAsP. <i>Materials Research Society Symposia Proceedings</i> , <b>1996</b> , 422, 255		3
6	Acceptor-Hydrogen Interaction in Ternary III-V Semiconductors. <i>Materials Science Forum</i> , <b>1995</b> , 196-201, 987-992	0.4	1
5	Bulk Growth of SiC [Review on Advances of SiC Vapor Growth for Improved Doping and Systematic Study on Dislocation Evolution] 1-31		2
4	Applicability of a Flat-Bed Birefringence Setup for the Determination of Threading Dislocations of Silicon Carbide Wafers. <i>Materials Science Forum</i> , <b>1062</b> , 113-118	0.4	
3	In Situ Monitoring of Unintentionally Released Nitrogen Gas in the Initial PVT Silicon Carbide Growth Process Using Mass Spectrometry. <i>Materials Science Forum</i> , <b>1062</b> , 79-83	0.4	

2	Large Area Growth of Cubic Silicon Carbide Using Close Space PVT by Application of Homoepitaxial Seeding. <i>Materials Science Forum</i> ,1062, 74-78	0.4	2
1	Chemical Vapor Deposition of 3C-SiC on [100] Oriented Silicon at Low Temperature &lt; 1200°C for Photonic Applications. <i>Materials Science Forum</i> ,1062, 119-124	0.4	1